

Silicon NPN Power Transistors

2SC3870

DESCRIPTION

- With TO-220Fa package
- High breakdown voltage
- Wide area of safe operation

APPLICATIONS

- For high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

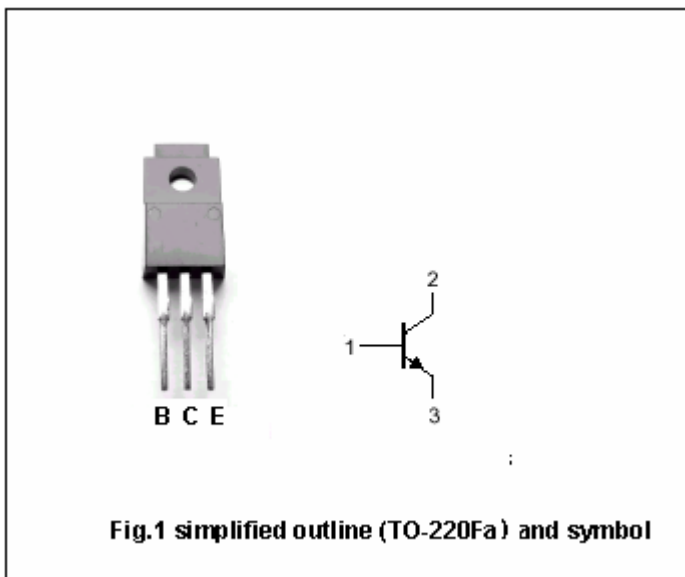


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	500	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current (DC)		7	A
$I_{CM}$	Collector current (pulse)		15	A
$I_B$	Base current (DC)		3	A
$P_C$	Collector power dissipation	$T_a=25$	2	W
		$T_C=25$	40	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## Silicon NPN Power Transistors

## 2SC3870

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.6A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.6A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	15			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V		30		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =3A ; I <sub>B</sub> =0.6A; I <sub>B2</sub> =-1.2A V <sub>CC</sub> =150V			0.7	μ s
t <sub>s</sub>	Storage time				2.0	μ s
t <sub>f</sub>	Fall time				0.3	μ s

PACKAGE OUTLINE

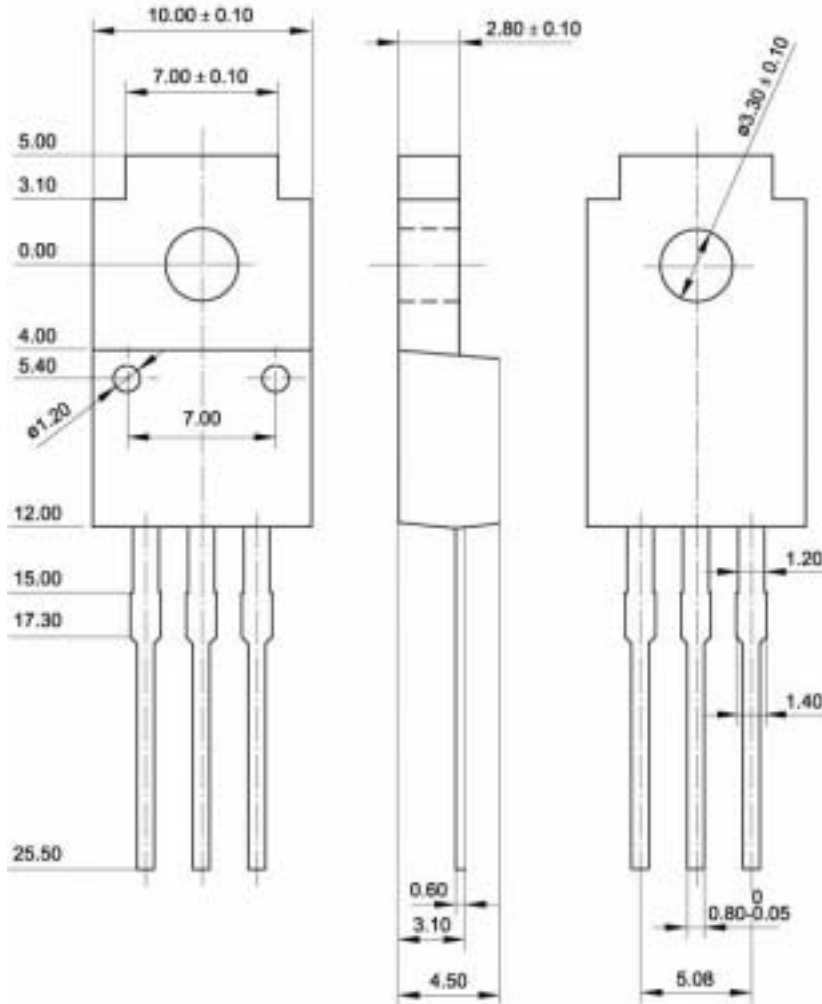


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)